

ABSTRACT

Disclosed are a semiconductor device and a method of fabricating the same. The semiconductor device includes a substrate including a cell disposing region and a first block border region, a plurality of gate electrodes on the cell disposing region and extending to the first block border region in a first direction to be parallel to each other, the gate electrodes including a first and second gate electrode, which are adjacent to each other, and a first connection structure on the first block border region, wherein the first connection structure is configured to physically connect the first and second gate electrodes to each other.

FIG. 5